TOSHIBA Infrared LED GaAs Infrared Emitter

TLN110(F)

Lead(Pb)-Free Remote-control Systems Opto-electronic Switches

- High radiant intensity: IE = 30 mW / sr (typ.)
- Excellent radiant-intensity linearity. Modulation by pulse operation and high frequency is possible.
- TPS703(F) PIN photodiode with resin to screen out visible light available as detector for remote control

Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Forward current	IF	100	mA
Forward current derating (Ta > 25°C)	ΔI _F / °C	-1.33	mA / °C
Pulse forward current	I _{FP} (Note 1)	1	Α
Reverse voltage	V_{R}	5	V
Power dissipation	P_{D}	150	mW
Operating temperature range	T _{opr}	-20~75	°C
Storage temperature range	T _{stg}	-30~100	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling

Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width ≤ 100µs, repetitive frequency = 100 Hz

Unit: mm 05 + 0.2(1.7) (1.2) 0.5 ± 0.1 0.5 ± 0.1 (): Reference value TOSHIBA 4-6C4

Weight: 0.32 g (typ.)

Pin Connection

2. Cathode

Optical And Electrical Characteristics (Ta = 25°C)

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Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V _F	I _F = 100mA	_	1.35	1.5	V
Reverse current	I _R	V _R = 5V	_	_	10	μΑ
Radiant intensity	ΙE	I _F = 50mA	15	30	_	mW/sr
Radiant power	PO	I _F = 50mA	_	9	_	mW
Capacitance	C _T	V _R = 0, f = 1MHz	_	20	_	pF
Peak emission wavelength	λP	I _F = 50mA	_	940	_	nm
Spectral line half width	Δλ	I _F = 50mA	_	45	_	nm
Half value angle	$\theta \frac{1}{2}$	I _F = 50mA	_	±8	_	۰

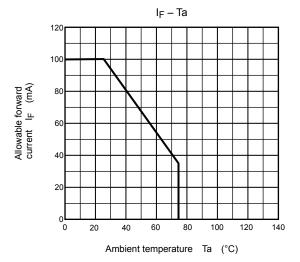
Precautions

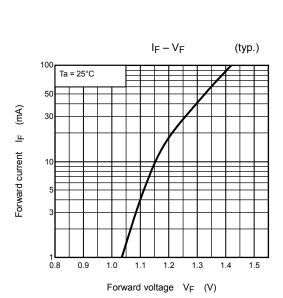
Please be careful of the followings.

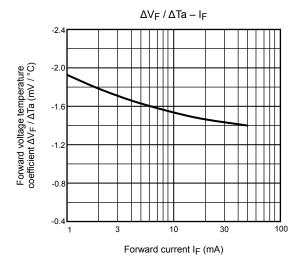
- 1. Soldering temperature : 260°C max Soldering time : 5s max
 - (Soldering must be performed under the stopper.)
- 2. When forming the leads, bend each lead under the 2mm from the body of the device. Soldering must be performed after the leads have been formed.
- 3. Radiant intensity falls over time due to the current which flows in the infrared LED. When designing a circuit, take into account this change in radiant power over time. The ratio of fluctuation in radiation intensity to fluctuation in optical output is 1:1.

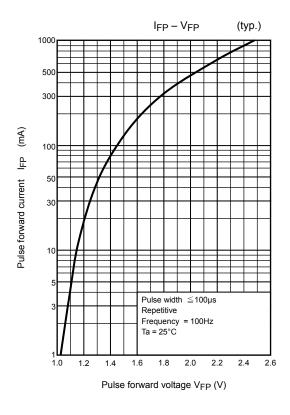
$$\frac{I_{E}(t)}{I_{E}(0)} = \frac{P_{O}(t)}{P_{O}(0)}$$

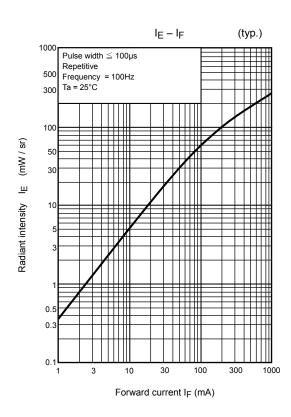
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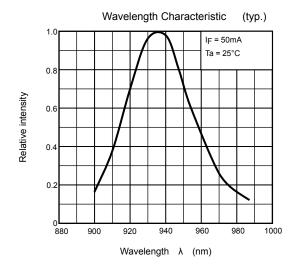


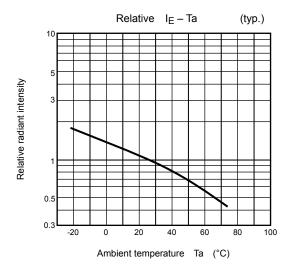






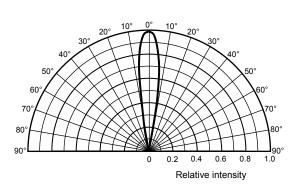
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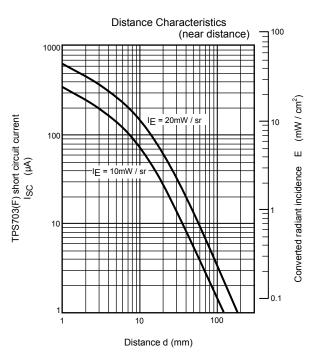




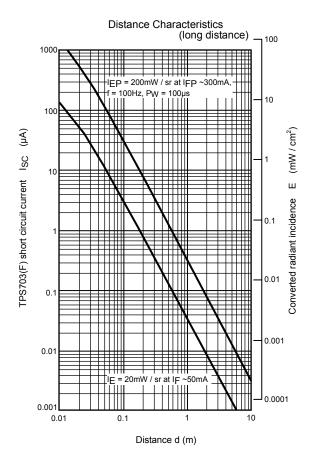
Radiation Pattern (typ.)

(Ta = 25°C)





| IFP - PW | 3000 | Ta = 25°C | Ta = 25°C



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RESTRICTIONS ON PRODUCT USE

20070701-EN

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